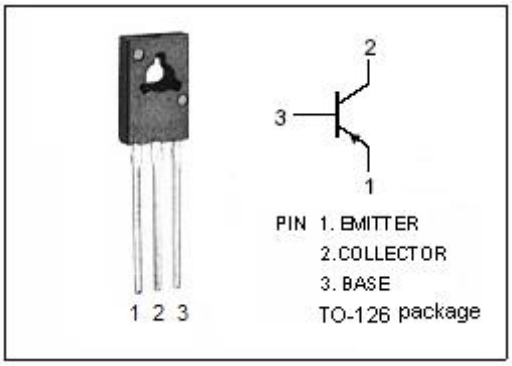
isc Silicon PNP Power Transistor 2SA1359

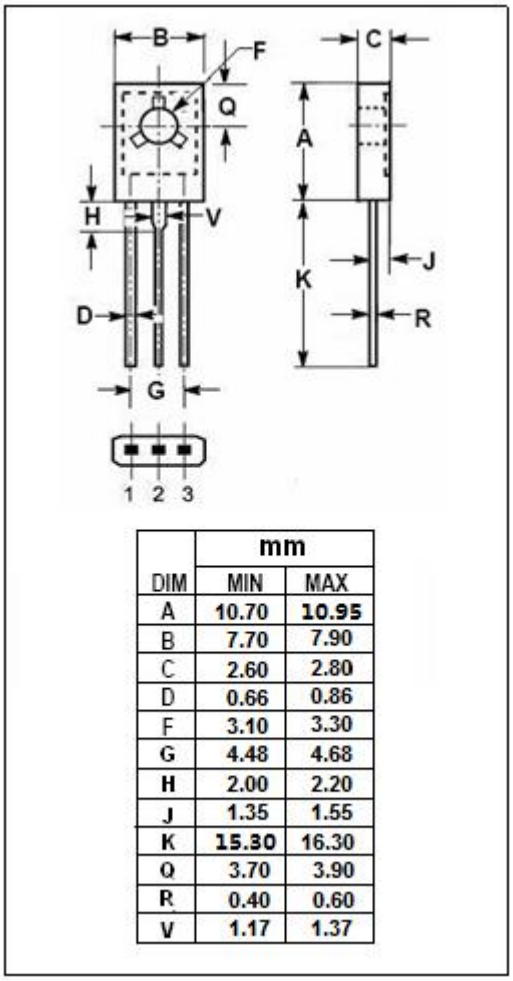
DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -40V (Min)
- Good Linearity of h_{FE}
- Complement to Type 2SC3422
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for audio frequency power amplifier and low speed switching applications.



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-3	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ T_a=25℃	1.5	W
	Total Power Dissipation @ T_C=25℃	10	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; I_B= 0	-40			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2A; I_B= -0.2A			-0.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -0.5A; V_{CE}= -2V			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0			-0.1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-0.1	μA
h_{FE-1}	DC Current Gain	I_C= -0.5A; V_{CE}= -2V	80		240	
h_{FE-2}	DC Current Gain	I_C= -2.5A; V_{CE}= -2V	25			
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A; V_{CE}= -2V		100		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1.0MHz		35		pF

◆ **h_{FE-1} Classifications**

O	Y
80-160	120-240